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AMENDMENT UNDER 37 C.F.R. § 1.111  
U.S. Application No. 09/826,851  
Attorney Docket Q63956

the depth of the concave portion is at least equal to the thickness of the substrate.

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7. (Amended) The semiconductor laser element according to any of claims 1 to 3,  
wherein said semiconductor laser element is a light source for exciting a solid laser.

*B3*

20. (Amended) The semiconductor laser element according to claim 18 or 19,  
wherein the groove is filled with a metal having a heat conductivity higher than the GaN  
substrate,

wherein the surface having the groove is flattened, and wherein,  
a heatsink is connected to the flattened surface.

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Please add the following new claim.

23. (New) A semiconductor laser element comprising  
a substrate,  
a plurality of semiconductor layers formed on the substrate, and  
a groove formed on one surface of the substrate, said one surface being opposite to the  
other surface having the semiconductor layers formed thereon, wherein  
the groove extends to the depth of the substrate, and wherein  
the groove is filled with a metal having a heat conductivity higher than the substrate.